



BSS127

N-CHANNEL ENHANCEMENT MODE FIELD MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
600V	160Ω @ V _{GS} = 10V	SC59 SOT23	70mA

Features

- Low Input Capacitance
- High BVDss rating for power application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Description

This new generation uses advanced planar technology MOSFET, provide excellent high Voltage and fast switching, making it ideal for small-Signal and level shift applications.

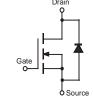
Applications

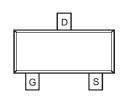
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Mechanical Data

- Case: SC59 / SOT23
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 ³
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)







Top View

Equivalent Circuit

Top View

SC59

Ordering Information (Note 4)

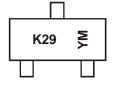
Part Number	Case	Packaging
BSS127SSN-7	SC59	3000/Tape & Reel
BSS127S-7	SOT23	3000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

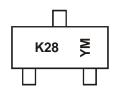
Marking Information





K29 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)



K28 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Χ		Υ		Z	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	600	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	50 40	mA
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	70 55	mA
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	45 35	mA
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	65 50	mA
Pulsed Drain Current @ T _{SP} = +25°C (Notes 7)			I _{DM}	0.16	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units
Power Dissipation, @T _A = 25°C (Note 5)	P_{D}	0.61	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	$R_{ hetaJA}$	204	°C/W
Power Dissipation, @T _{SP} = 25°C (Note 6)	P_{D}	1.25	W
Thermal Resistance, Junction to Ambient @T _{SP} = +25°C (Note 6)	$R_{ heta JSA}$	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

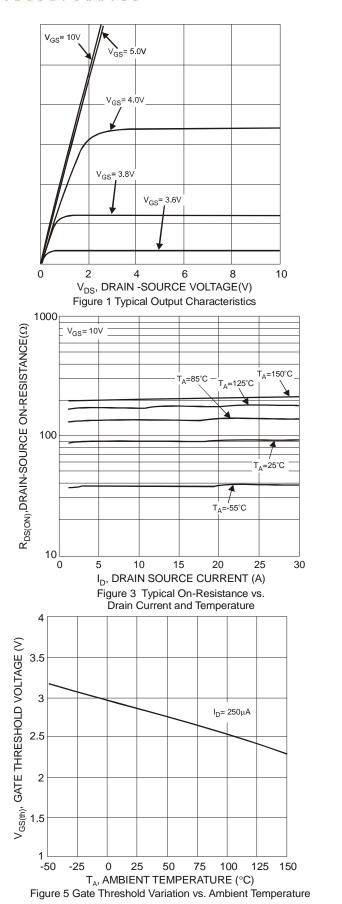
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

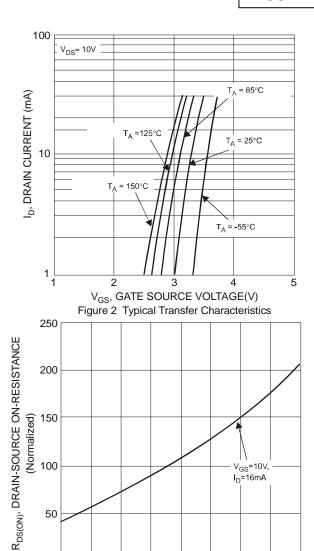
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
DFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	600	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	0.1	μA	$V_{DS} = 600V, V_{GS} = 0V$	
Gate-Body Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(th)}	3	_	4.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	D	_	80	160	Ω	$V_{GS} = 10V, I_D = 16mA$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	95	190	2.2	$V_{GS} = 5.0V, I_D = 16mA$	
Forward Transfer Admittance	Y _{fs}		76	_	mS	$V_{DS} = 10V, I_D = 16mA$	
Diode Forward Voltage	V_{SD}	1	_	1.5	V	$V_{GS} = 0V$, $I_S = 16mA$	
DYNAMIC CHARACTERISTICS (Note 9)		_					
Input Capacitance	C _{iss}	1	21.8	_			
Output Capacitance	Coss	_	2.2	_	pF	$V_{DS} = 25V$, $V_{GS} = 0V$, $f = 1.0MHz$	
Reverse Transfer Capacitance	C_{rss}	_	0.3	_			
Total Gate Charge	Qg	_	1.08	_		101/1/	
Gate-Source Charge	Q_{gs}	_	0.08	_	nC	$V_{GS} = 10V, V_{DD} = 300V,$ $I_{D} = 0.01A$	
Gate-Drain Charge	Q_{gd}	_	0.50	_		ID = 0.01A	
Turn-On Delay Time	t _{D(on)}	_	5.0	_	ns	V 000V V 40V	
Turn-On Rise Time	t _r	_	7.2	_	ns	$V_{DD} = 300V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(off)}	_	28.7	_	ns	$R_{GEN} = 6\Omega$, $I_D = 10$ mA	
Turn-Off Fall Time	t _f	_	168	_	ns	TID = TOTILA	
Reverse Recovery Time	T _{rr}	_	131	_	ns	V _R =300 V, I _F =0.016 A,	
Reverse Recovery Charge	Q _{rr}	-	32	_	nC	di/dt = 100A/µs	

Notes:

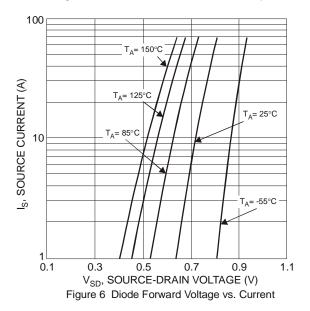
- 5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided. 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
- 7. Repetitive rating, pulse width limited by junction temperature, $10\mu s$ pulse, duty cycle = 1%.
- Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.







V_{GS}=10V, I_D=16mA 100 -50 25 50 75 100 T_J , JUNCTION TEMPERATURE (°C) Figure 4 On-Resistance Variation with Temperature





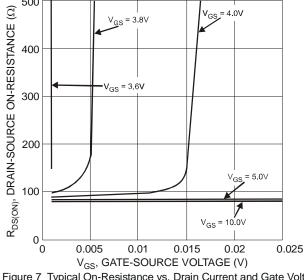


Figure 7 Typical On-Resistance vs. Drain Current and Gate Voltage

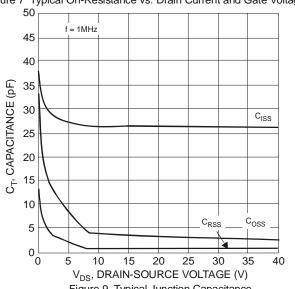


Figure 9 Typical Junction Capacitance

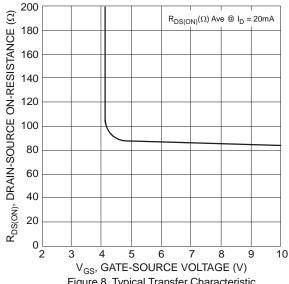


Figure 8 Typical Transfer Characteristic

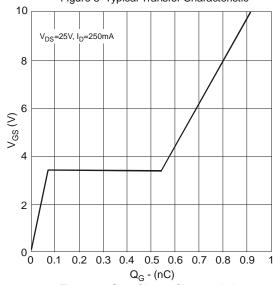
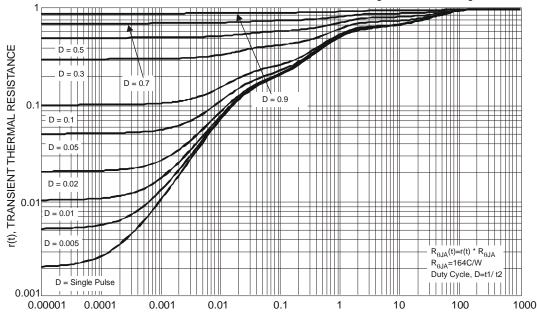


Figure 10 Gate Charge Characteristics



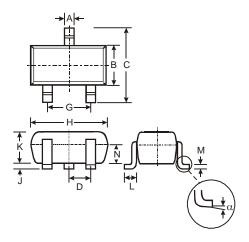
t1, PULSE DURATION TIME (sec) Figure 11 Transient Thermal Resistance



Package Outline Dimensions

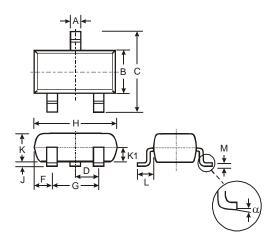
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

SC59



SC59					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	-	-	0.95		
G	-	-	1.90		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
N	0.70	0.80	0.75		
α	0°	8°	-		
All	Dimens	ions in	mm		

SOT23

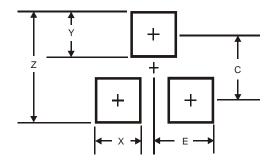


	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
M	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SC59

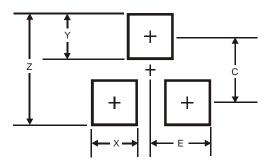


Dimensions	Value (in mm)
Z	3.4
Х	0.8
Υ	1.0
С	2.4
E	1.35



Suggested Pad Layout (cont.)

SOT23



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35

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